750 MHz Voltage Feedback Op Amp with Fast Enable Feature

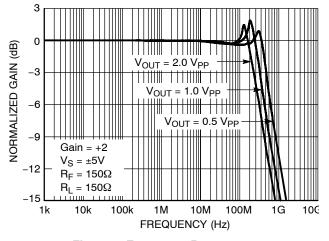
NCS2552 is a 750 MHz voltage feedback monolithic operational amplifier featuring high slew rate and low differential gain and phase error. The voltage feedback architecture allows for a superior bandwidth and low power consumption. This device features an enable pin.

Features

- $-3.0 \text{ dB Small Signal BW} (A_V = +2.0, V_O = 0.5 V_{p-p}) 750 \text{ MHz Typ}$
- Slew Rate 1700 V/ μ s
- Fast Enable Time 5.0 ns
- Supply Current 13 mA
- Input Referred Voltage Noise 5.0 nV/\sqrt{Hz}
- THD -64 dBc (f = 5.0 MHz, $V_0 = 2.0 V_{p-p}$)
- Output Current 100 mA
- Pin Compatible with EL5157, AD8057
- This is a Pb–Free Device

Applications

- Line Drivers
- Radar/Communication Receivers

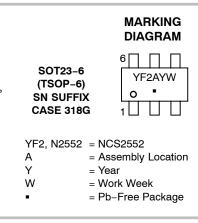




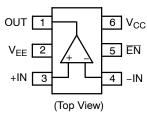


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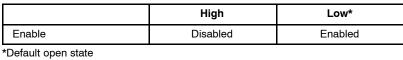
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

PIN FUNCTION DESCRIPTION

Pin (SOT23/SC70)	Symbol	Function	Equivalent Circuit
1	OUT	Output	
2	V _{EE}	Negative Power Supply	
3	+IN	Non-inverted Input	V _{CC} ESD -IN ESD V _{EE}
4	–IN	Inverted Input	See Above
6	V _{CC}	Positive Power Supply	
5	EN	Enable	

ENABLE PIN TRUTH TABLE





ATTRIBUTES

Characteristics	Value
ESD Human Body Model Machine Model Charged Device Model	2.0 kV 200 V 1.0 kV
Moisture Sensitivity (Note 1)	Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in

1. For additional information, see Application Note AND8003/D.

MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Power Supply Voltage	V _S	11	Vdc
Input Voltage Range	VI	$\leq V_{S}$	Vdc
Input Differential Voltage Range	V _{ID}	$\leq V_{S}$	Vdc
Output Current	Ι _Ο	100	mA
Maximum Junction Temperature (Note 2)	TJ	150	°C
Operating Ambient Temperature	T _A	-40 to +85	°C
Storage Temperature Range	T _{stg}	−60 to +150	°C
Power Dissipation	PD	(See Graph)	mW
Thermal Resistance, Junction-to-Air	$R_{\theta JA}$	158	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

2. Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded.

MAXIMUM POWER DISSIPATION

The maximum power that can be safely dissipated is limited by the associated rise in junction temperature. For the plastic packages, the maximum safe junction temperature is 150°C. If the maximum is exceeded momentarily, proper circuit operation will be restored as soon as the die temperature is reduced. Leaving the device in the "overheated" condition for an extended period can result in device damage.

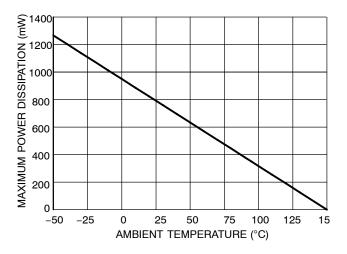


Figure 3. Power Dissipation vs. Temperature

AC ELECTRICAL CHARACTERISTICS (V _{CC} = +5.0 V, V _{EE} = -5.0 V, T _A = -40°C to +85°C, R _L = 150 Ω to GND, R _F = 150 Ω	,
A_V = +2.0, Enable is left open, unless otherwise specified).	

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
FREQUENC	Y DOMAIN PERFORMANCE			•		
BW	Bandwidth 3.0 dB Small Signal 3.0 dB Large Signal	$\begin{array}{l} A_V = +2.0, \ V_O = 0.5 \ V_{p-p} \\ A_V = +2.0, \ V_O = 2.0 \ V_{p-p} \end{array}$		750 350		MHz
GF _{0.1dB}	0.1 dB Gain Flatness Bandwidth	A _V = +2.0		40		MHz
dG	Differential Gain	A_V = +2.0, R_L = 150 Ω,f = 3.58 MHz		0.07		%
dP	Differential Phase	A_V = +2.0, R_L = 150 Ω,f = 3.58 MHz		0.01		٥
TIME DOM/	AIN RESPONSE					
SR	Slew Rate	A_V = +2.0, V_{step} = 2.0 V		1700		V/µs
t _s	Settling Time 0.1%	A _V = +2.0, V _{step} = 2.0 V		10		ns
t _r t _f	Rise and Fall Time	(10%–90%) A_V = +2.0, V_{step} = 2.0 V		2.0		ns
t _{ON}	Turn-on Time			5.0		ns
t _{OFF}	Turn-off Time			15		ns
HARMONIC	/NOISE PERFORMANCE					
THD	Total Harmonic Distortion	f = 5.0 MHz, V_O = 2.0 V_{p-p}		-64		dB
HD2	2nd Harmonic Distortion	f = 5.0 MHz, V_O = 2.0 V_{p-p}		-65		dBc
HD3	3rd Harmonic Distortion	f = 5.0 MHz, V_O = 2.0 V_{p-p}		-75		dBc
IP3	Third-Order Intercept	$f = 10 \text{ MHz}, \text{ V}_{\text{O}} = 1.0 \text{ V}_{\text{p-p}}$		40		dBm
SFDR	Spurious-Free Dynamic Range	f = 5.0 MHz, V_0 = 2.0 V_{p-p}		55		dBc
e _N	Input Referred Voltage Noise	f = 1.0 MHz		5.0		nV/\sqrt{Hz}
i _N	Input Referred Current Noise	f = 1.0 MHz		4.0		pA/√Hz

DC ELECTRICAL CHARACTERISTICS (V_{CC} = +5.0 V, V_{EE} = -5.0 V, T_A = -40°C to +85°C, R_L = 150 Ω to GND, R_F = 150 Ω , A_V = +2.0, Enable is left open, unless otherwise specified).Closed Loop Open Loop

Symbol	Characteristic	Conditions	Min	Тур	Мах	Unit
DC PERFO	RMANCE					
V _{IO}	Input Offset Voltage		-10	0	+10	mV
$\Delta V_{IO} / \Delta T$	Input Offset Voltage Temperature Coefficient			6.0		μV/°C
I _{IB}	Input Bias Current	V _O = 0 V		±3.2	±20	μA
$\Delta I_{IB} / \Delta T$	Input Bias Current Temperature Coefficient	V _O = 0 V		± 40		nA/°C
V _{IH}	Input High Voltage (Enable) (Note 3)		3.0			V
VIL	Input Low Voltage (Enable) (Note 3)				1.0	V
	ARACTERISTICS		•		•	
V_{CM}	Input Common Mode Voltage Range (Note 3)		±3.0	±3.2		V
CMRR	Common Mode Rejection Ratio	(See Graph)	40	50		dB
R _{IN}	Input Resistance			4.5		MΩ
C _{IN}	Differential Input Capacitance			1.0		pF
ОЛТЬПТ С	HARACTERISTICS					
R _{OUT}	Output Resistance	Closed Loop Open Loop		0.1 13		Ω
Vo	Output Voltage Range		±3.0	±4.0		V
Ι _Ο	Output Current		± 50	±100		mA
POWER SL	JPPLY					
Vs	Operating Voltage Supply			10		V
I _{S,ON}	Power Supply Current – Enabled		5.0	13	17	mA
I _{S,OFF}	Power Supply Current – Disabled			0.5	0.8	mA
PSRR	Power Supply Rejection Ratio	(See Graph)	40	56		dB

3. Guaranteed by design and/or characterization.

AC ELECTRICAL CHARACTERISTICS (V _{CC} = +2.5 V, V _{EE} = -2.5 V, T _A = -40°C to +85°C, R _L = 150 Ω to GND, R _F = 150 Ω	,
A _V = +2.0, Enable is left open, unless otherwise specified).	

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
FREQUENC	Y DOMAIN PERFORMANCE					-
BW	Bandwidth 3.0 dB Small Signal 3.0 dB Large Signal	$\begin{array}{l} A_V = +2.0, \ V_O = 0.5 \ V_{p-p} \\ A_V = +2.0, \ V_O = 1.0 \ V_{p-p} \end{array}$		550 200		MHz
GF _{0.1dB}	0.1 dB Gain Flatness Bandwidth	A _V = +2.0		35		MHz
dG	Differential Gain	A_V = +2.0, R_L = 150 Ω , f = 3.58 MHz		0.07		%
dP	Differential Phase	A_V = +2.0, R_L = 150 Ω , f = 3.58 MHz		0.02		0
TIME DOM	AIN RESPONSE					-
SR	Slew Rate	A _V = +2.0, V _{step} = 1.0 V		900		V/µs
t _s	Settling Time 0.1%	A _V = +2.0, V _{step} = 1.0 V		10		ns
t _r t _f	Rise and Fall Time	(10%-90%) A _V = +2.0, V _{step} = 1.0 V		1.7		ns
t _{ON}	Turn-on Time			5.0		ns
t _{OFF}	Turn-off Time			15		ns
HARMONIC	/NOISE PERFORMANCE					
THD	Total Harmonic Distortion	f = 5.0 MHz, V_O = 1.0 V_{p-p}		-60		dB
HD2	2nd Harmonic Distortion	f = 5.0 MHz, V_O = 1.0 V_{p-p}		-65		dBc
HD3	3rd Harmonic Distortion	f = 5.0 MHz, V_O = 1.0 V_{p-p}		-63		dBc
IP3	Third-Order Intercept	f = 10 MHz, $V_O = 0.5 V_{p-p}$		35		dBm
SFDR	Spurious-Free Dynamic Range	f = 5.0 MHz, V_0 = 1.0 V_{p-p}		63		dBc
e _N	Input Referred Voltage Noise	f = 1.0 MHz		5.0		nV/\sqrt{Hz}
i _N	Input Referred Current Noise	f = 1.0 MHz		4.0		pA/\sqrt{Hz}

DC ELECTRICAL CHARACTERISTICS (V _{CC} = +2.5 V, V _{EE} = -2.5 V, T _A = -40°C to +85°C, R _L = 150 Ω to GND, R _F = 150 Ω ,	
A _V = +2.0, Enable is left open, unless otherwise specified).	

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
DC PERFO	RMANCE		-			
V _{IO}	Input Offset Voltage		-10	0	+10	mV
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Temperature Coefficient			6.0		μV/°C
I _{IB}	Input Bias Current	V _O = 0 V		± 3.2	±20	μA
$\Delta I_{IB} / \Delta T$	Input Bias Current Temperature Coefficient	V _O = 0 V		± 40		nA/°C
V _{IH}	Input High Voltage (Enable) (Note 3)		1.5			V
V _{IL}	Input Low Voltage (Enable) (Note 3)				0.5	V
INPUT CHA	RACTERISTICS		-			
V_{CM}	Input Common Mode Voltage Range (Note 3)		±1.1	±1.6		V
CMRR	Common Mode Rejection	(See Graph)	40	50		dB

CMRR	Ratio	(See Graph)	40	50	dВ
R _{IN}	Input Resistance			4.5	MΩ
C _{IN}	Differential Input Capacitance			1.0	pF

OUTPUT CHARACTERISTICS

R _{OUT}	Output Resistance	Closed Loop Open Loop		0.1 13	Ω
Vo	Output Voltage Range		±1.1	±1.6	V
Ι _Ο	Output Current		±50	±100	mA

POWER SUPPLY

VS	Operating Voltage Supply			5.0		V
I _{S,ON}	Power Supply Current – Enabled		5.0	11.5	17	mA
I _{S,OFF}	Power Supply Current – Disabled			0.5	0.8	mA
PSRR	Power Supply Rejection Ratio	(See Graph)	40	56		dB

4. Guaranteed by design and/or characterization.

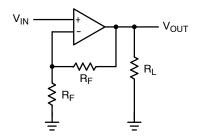
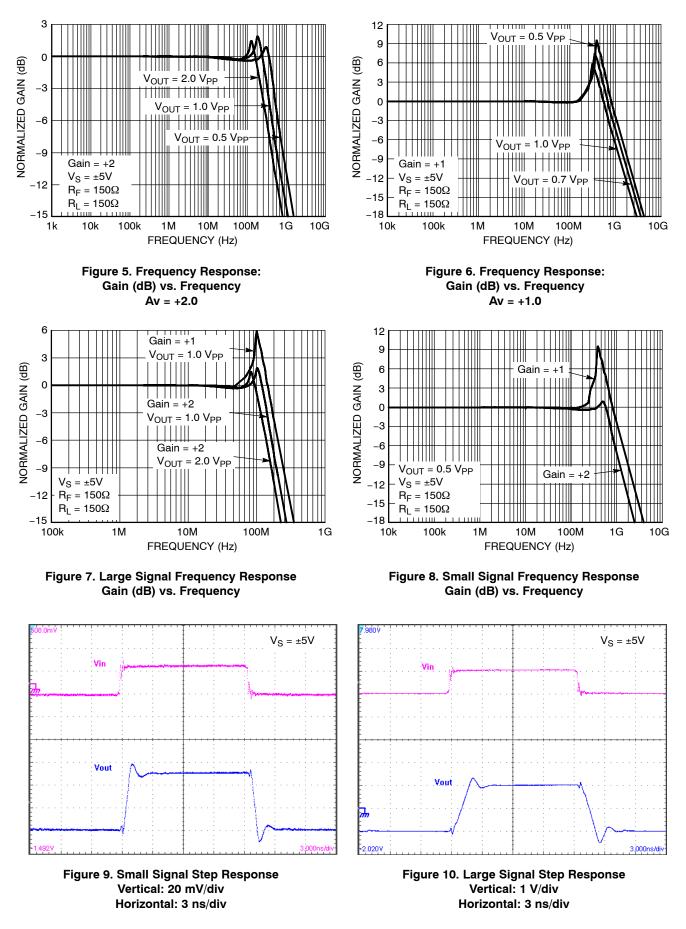


Figure 4. Typical Test Setup (A_V = +2.0, R_F = 1.0 k Ω , R_L = 100 Ω)



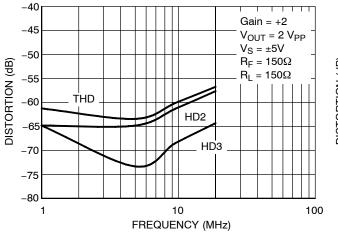


Figure 11. THD, HD2, HD3 vs. Frequency

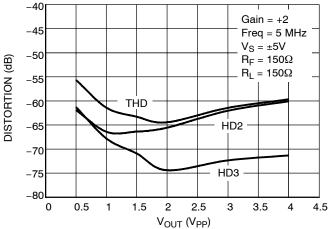


Figure 12. THD, HD2, HD3 vs. Output Voltage

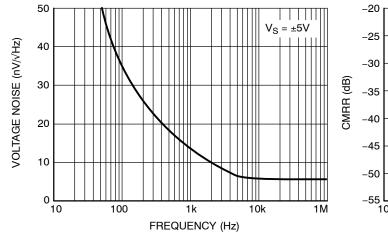


Figure 13. Input Referred Voltage Noise vs. Frequency

0

-10

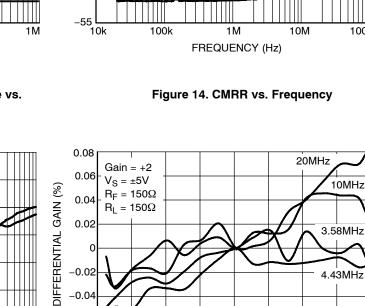
-20

-30

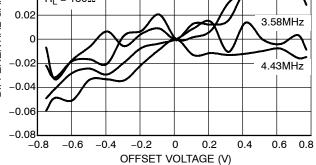
-40

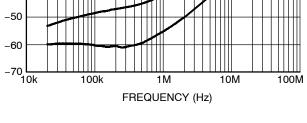
PSRR (dB)

 $V_{\rm S} = \pm 5V$



V_S = ±5V

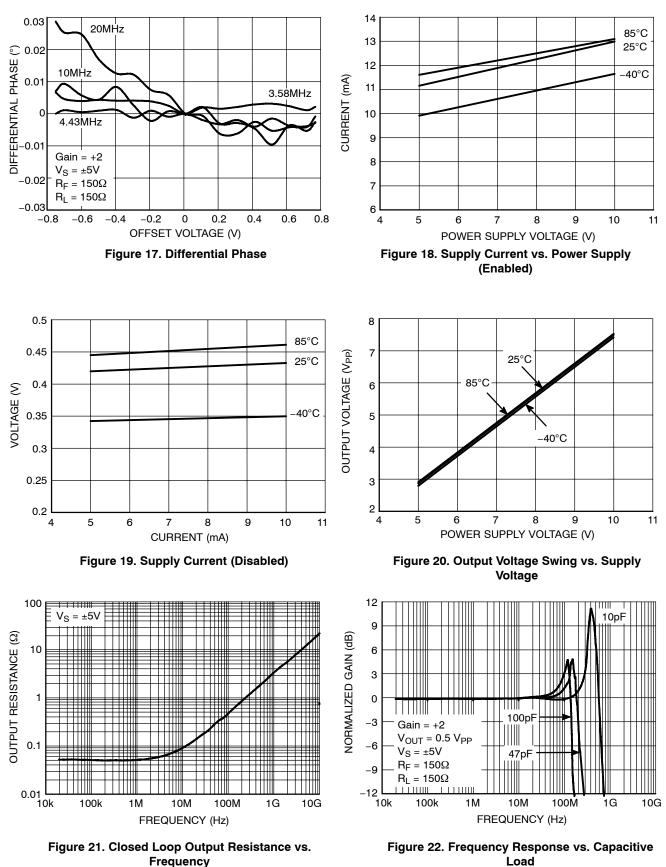








100M



Frequency

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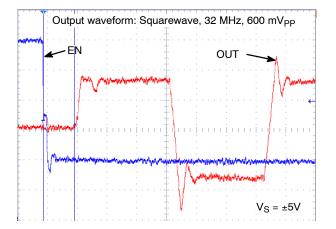


Figure 23. Turn ON Time Delay Vertical: 500 mV/div (Enable), 200 mV/div (Output) Horizontal: 5 ns/div

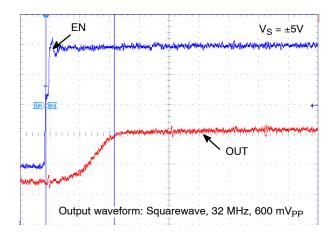


Figure 24. Turn OFF Time Delay Vertical: 500 mV/div (Enable), 200 mV/div (Output) Horizontal: 5 ns/div

Printed Circuit Board Layout Techniques

Proper high speed PCB design rules should be used for all wideband amplifiers as the PCB parasitics can affect the overall performance. Most important are stray capacitances at the output and inverting input nodes as it can effect peaking and bandwidth. A space (3/16" is plenty) should be left around the signal lines to minimize coupling. Also, signal lines connecting the feedback and gain resistors should be short enough so that their associated inductance does not cause high frequency gain errors. Line lengths less than 1/4" are recommended.

Video Performance

This device designed to provide good performance with NTSC, PAL, and HDTV video signals. Best performance is obtained with back terminated loads as performance is degraded as the load is increased. The back termination reduces reflections from the transmission line and effectively masks transmission line and other parasitic capacitances from the amplifier output stage.

ESD Protection

All device pins have limited ESD protection using internal diodes to power supplies as specified in the attributes table (see Figure 25). These diodes provide moderate protection

to input overdrive voltages above the supplies. The ESD diodes can support high input currents with current limiting series resistors. Keep these resistor values as low as possible since high values degrade both noise performance and frequency response. Under closed–loop operation, the ESD diodes have no effect on circuit performance. However, under certain conditions the ESD diodes will be evident. If the device is driven into a slewing condition, the ESD diodes will clamp large differential voltages until the feedback loop restores closed–loop operation. Also, if the device is powered down and a large input signal is applied, the ESD diodes will conduct.

NOTE: Human Body Model for +IN and –IN pins are rated at 0.8kV while all other pins are rated at 2.0kV.

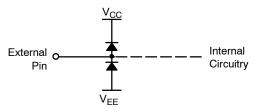


Figure 25. Internal ESD Protection

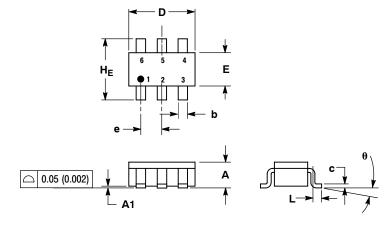
ORDERING INFORMATION

Device	Package	Shipping [†]		
NCS2552SNT1G	SOT23-6 (TSOP-6) (Pb-Free)	3000 Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE S

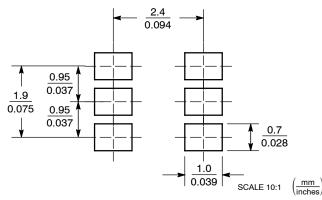


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI V14 5M 1982

- ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- MAXIMUM LEAD THICKNESS INCLUDEL
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- BASE MATERIAL.4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE
 - BURRS.

	м	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.90	1.00	1.10	0.035	0.039	0.043	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.25	0.38	0.50	0.010	0.014	0.020	
С	0.10	0.18	0.26	0.004	0.007	0.010	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.30	1.50	1.70	0.051	0.059	0.067	
е	0.85	0.95	1.05	0.034	0.037	0.041	
L	0.20	0.40	0.60	0.008	0.016	0.024	
HE	2.50	2.75	3.00	0.099	0.108	0.118	
θ	0°	-	10°	0°	-	10°	

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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